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FIS919990263US2

Claims 1-20 (Cancelled).

21. (Currently Amended) The metallization insulating structure of claim 32 ~~20~~ further comprising a capping layer on the substrate, underlying the first layer.
22. (Currently Amended) The metallization insulating structure according to claim 32 ~~20~~ wherein the fluorine containing insulating layer comprises a material selected from the group consisting of fluorinated silicon oxide, fluorinated amorphous carbon, fluorinated diamondlike carbon and fluorinated organic polymers.
23. (Currently Amended) The metallization insulating structure according to claim 32 ~~20~~ wherein the substantially fluorine free insulating layer comprises undoped silicon glass.
24. (Currently Amended) The metallization insulating structure according to claim 21 wherein the capping layer comprises a material selected from the group consisting of silicon nitride, silicon carbide and hydrogenated silicon carbide, or combinations thereof.

Claims 25-26 (Cancelled)

27. (Previously presented) The metallization structure of claim 21, wherein the metal structure extends through the capping layer such that the height of the structure is greater than  $h_i + h_f$ .

Claim 28 (Canceled)

29. (Previously presented) The structure of claim 21 wherein the metal structure is in contact with the underlying wires through the capping layer.

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30. (Currently Amended) The structure of claim ~~20~~ 32, a middle portion of the via contacted by the first layer.
31. (Previously presented) The structure of claim 30, a lower portion of the via contacted by one of the first layer and a capping layer.
32. (Currently Amended) A metallization insulating structure, comprising:  
a substantially planar substrate having wires therein;  
a first layer, the first layer a substantially fluorine free insulating layer  
formed on the substrate, having a height,  $h_i$ ;  
a second layer, the second layer a fluorine containing insulating layer  
formed directly on the first layer, having a height  $h_f$ , an interface between said  
first and second layer being substantially planar; and  
a metal structure of at least height  $h_i + h_f$  formed in the first and second  
layer, the metal structure extending to the substrate, the metal structure  
comprising a line and a via, a bottom of the line and an upper portion of the via  
contacted by the second layer The structure of claim 20, the line having a height  $h_l$  less than the overall height of the second layer  $h_f$ .
33. (Previously presented) The structure of claim 32, the via having a height  $h_v$  greater than the height of the first layer  $h_i$ .
34. (Previously presented) The structure of claim 33, the metal structure having a height  $h_t$  equivalent to height of the line  $h_l$  plus the height of the via  $h_v$ .
35. (Previously presented) The structure of claim 34, wherein the height of the first layer  $h_i$  is substantially less than the height of the via  $h_v$ .